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wherein the first thin film transistor is a p-type thin film transistor while the second thin film transistor is an n-type thin film transistor.

19.(New) A method according to claim 14, further comprising:

forming an insulating film over the first and second crystalline semiconductor islands, the first and second gate electrodes and the gate insulating film;

forming at least an electrode connected to one selected from the group consisting of the first source region, the first drain region, the second source region and the second drain region. --

In the drawings:

Please substitute Figure 3F with corrected Figure 3F.